

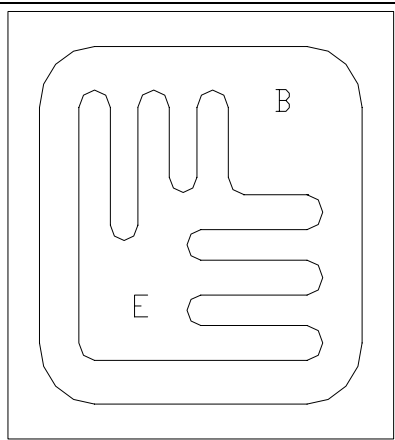
## BC807B Silicon PNP Epitaxial Transistor

Description: The BC807B is designed for audio frequency general amplifier applications.

Features: ●Excellent  $h_{FE}$  Linearity

●Complementary to BC817B

### Chip Appearance

	Chip Size		490um × 490um
	Chip Thickness		210 ± 20um
	Bonding Pad Size	Base	110um × 110um
		Emitter	110um × 110um
	Front Metal		Al
	Backside Metal		Au
	Scribe line width		55um
	Wafer Size		6 inch

### Electrical Characteristics( Ta=25°C )

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB}=-45V, I_E=0$		-0.1	uA
Emitter Cutoff Current	$I_{EBO}$	$V_{EB}=-5V, I_C=0$		-0.1	uA
Collector-Base Breakdown Voltage	$BV_{CBO}$	$I_C=-0.1mA$	-50		V
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	$I_C=-1mA$	-45		V
Emitter-Base Breakdown Voltage	$BV_{EBO}$	$I_E=-0.1mA$	-5.0		V
DC Current Gain	$h_{FE}$	$V_{CE}=-1V, I_C=-100mA$	120	560	
Collector Saturation Voltage	$V_{CE(sat)}$	$I_C=-500mA, I_B=-50mA$		-0.6	V